

N-Channel Enhancement Mode Power MOSFET TDM2306

DESCRIPTION

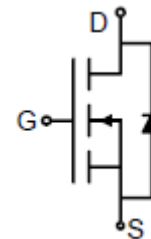
The TDM2306 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V.

GENERAL FEATURES

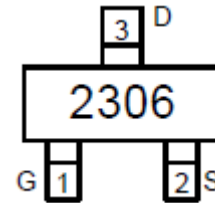
- $V_{DS} = 30V, I_D = 5A$
 $R_{DS(ON)} < 50m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 35m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 30m\Omega @ V_{GS}=10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23 top view

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	5	A
Drain Current-Pulsed (Note 1)	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.38	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	90	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA

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TDM2306

Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5		1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=2.5V, I_D=2.6A$			50	m Ω
		$V_{GS}=4.5V, I_D=5A$			35	m Ω
		$V_{GS}=10V, I_D=5A$			30	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$		13		S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$		660	1050	PF
Output Capacitance	C_{oss}			90		PF
Reverse Transfer Capacitance	C_{rss}			70		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=1A,$ $V_{GS}=10V, R_{GEN}=3.3\Omega$ $R_D=3\Omega$		6		nS
Turn-on Rise Time	t_r			20		nS
Turn-Off Delay Time	$t_{d(off)}$			20		nS
Turn-Off Fall Time	t_f			3		nS
Total Gate Charge	Q_g	$V_{DS}=16V, I_D=5A, V_{GS}=4.5V$		8.5	15	nC
Gate-Source Charge	Q_{gs}			1.5		nC
Gate-Drain Charge	Q_{gd}			3.2		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=1.2A$			1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

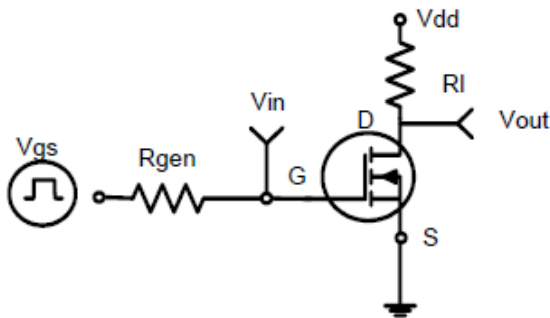


Figure 1: Switching Test Circuit

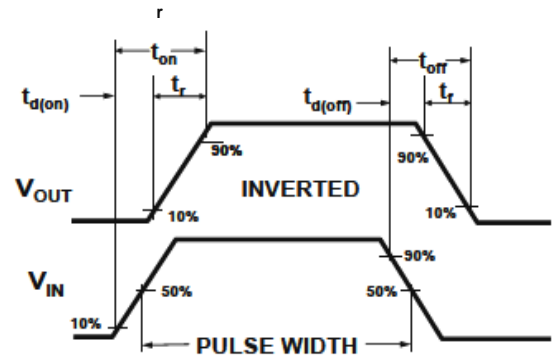


Figure 2: Switching Waveforms

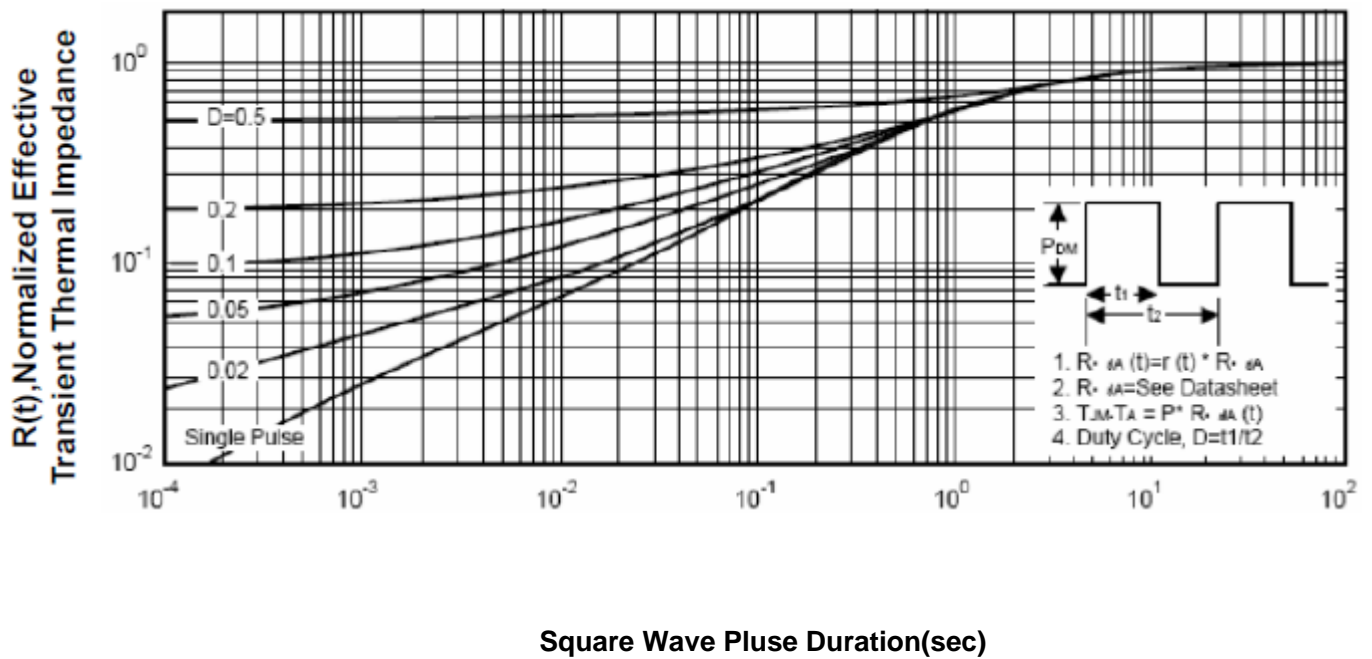
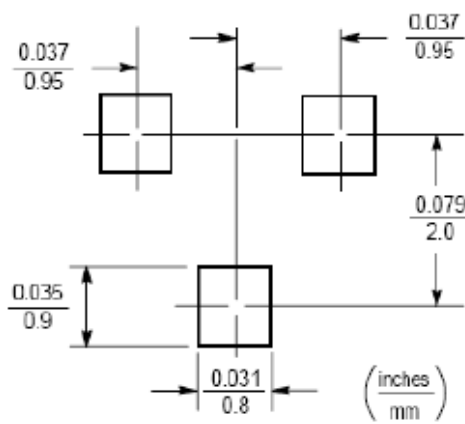
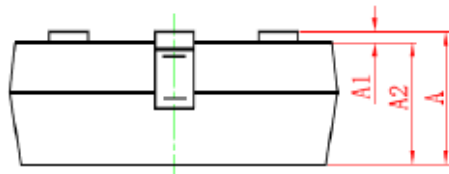
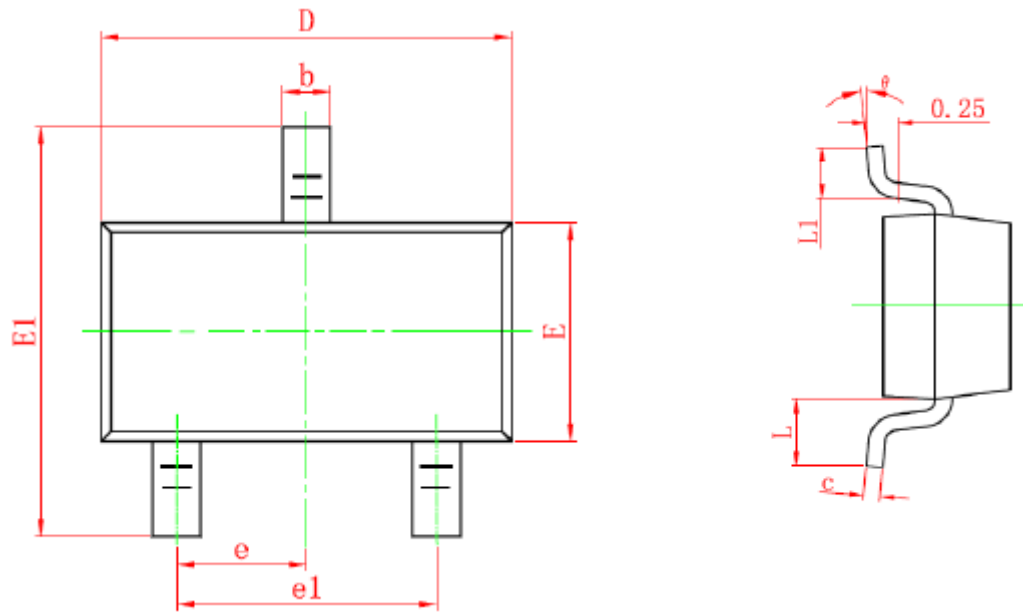


Figure 3: Normalized Maximum Transient Thermal Impedance

SOT-23 PACKAGE INFORMATION



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°